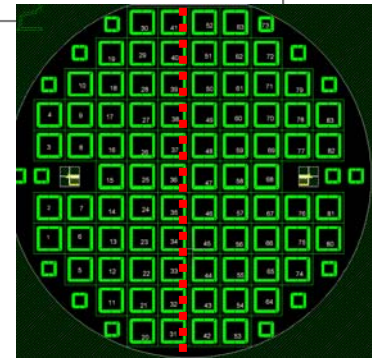
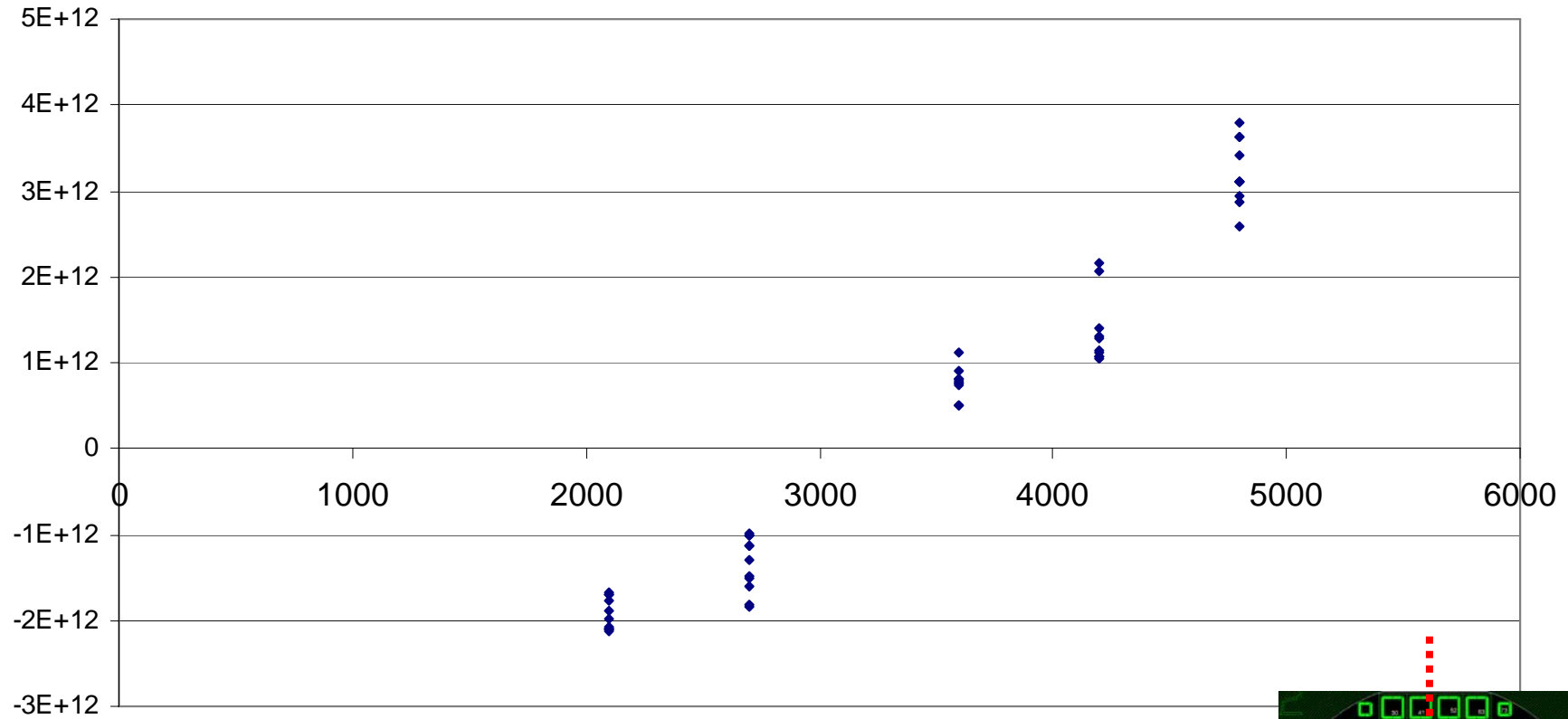


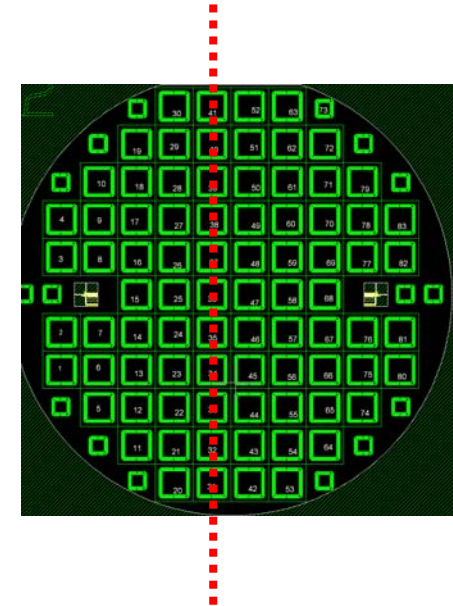
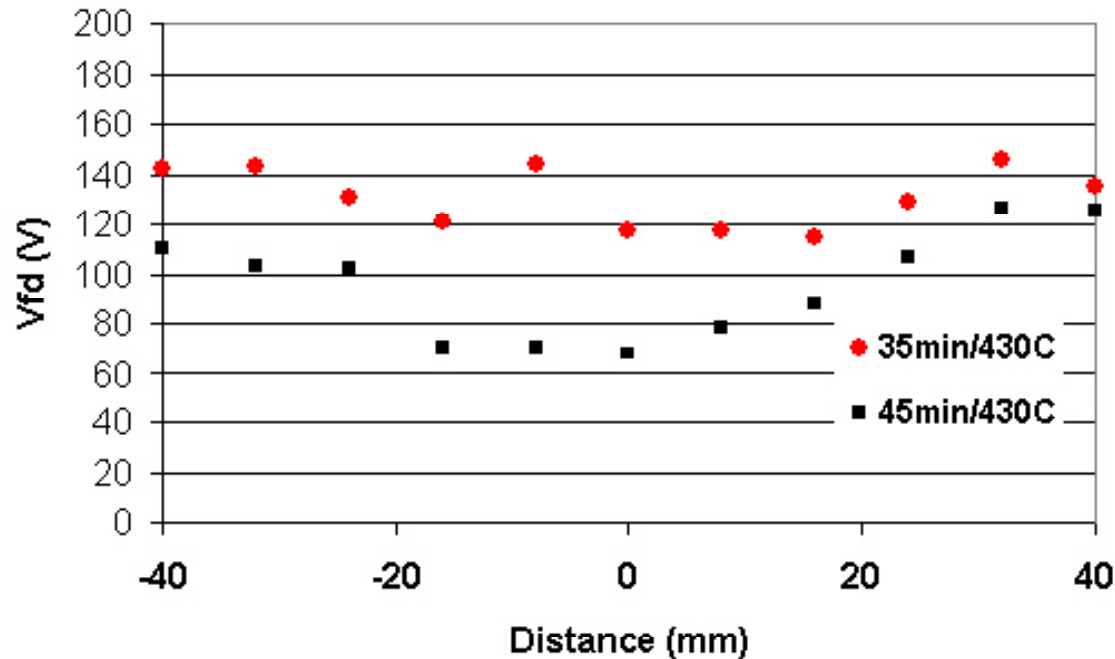
I-V/C-V results with p and n-type CZ devices

- *TD generation in MCz-si
- *Proton irradiation results
- *Annealing of MCz-Si
- *Processing issues
- *Mask sets in Helsinki

TD generation



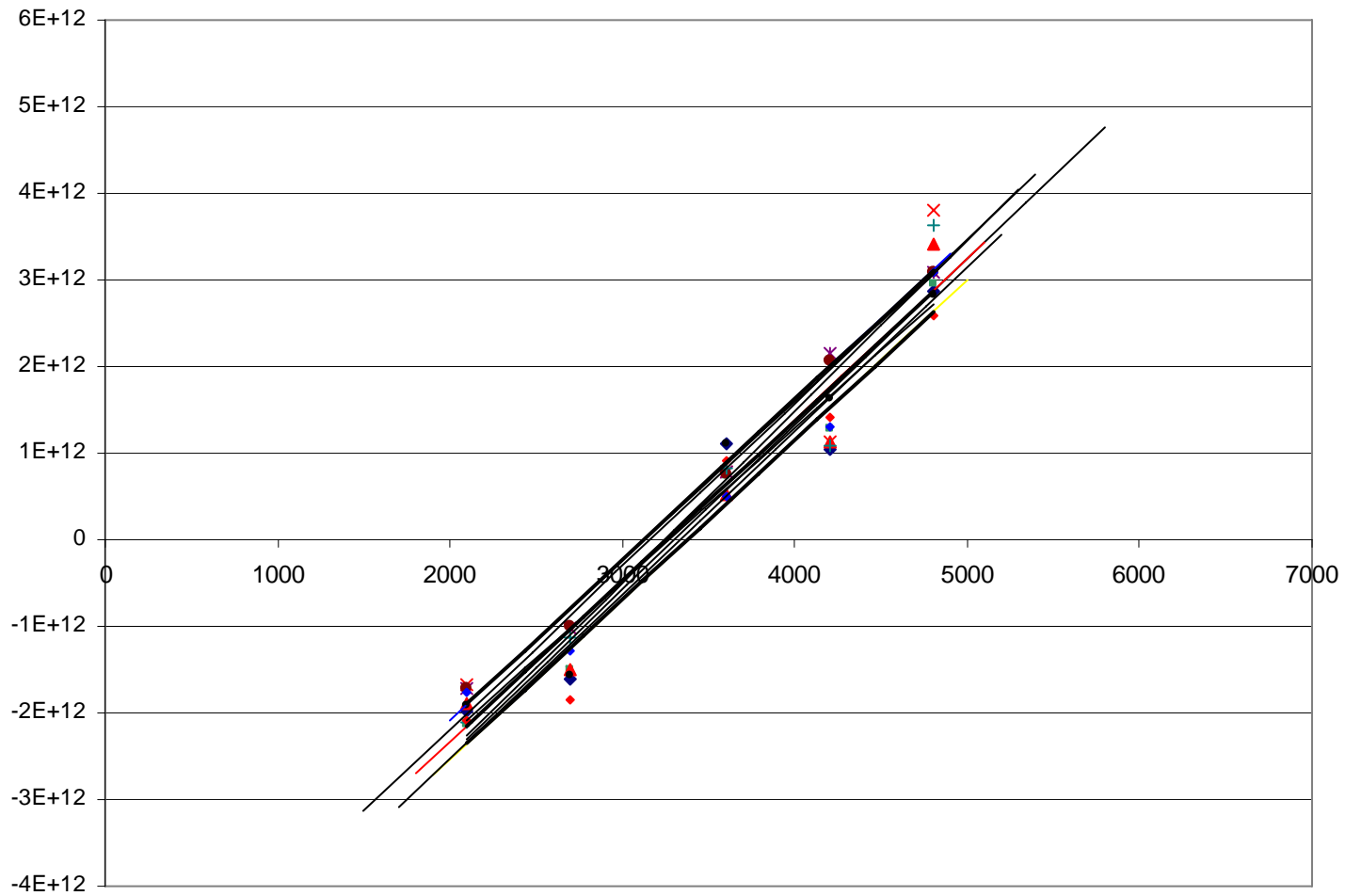
Thermal Donor generation (Homogeneity)



• We have not observed enhanced TD generation when the passivation was made by PECVD (Plasma Enhanced CVD) Si_3N_4 @300°C, which contains H_2 10-30%.

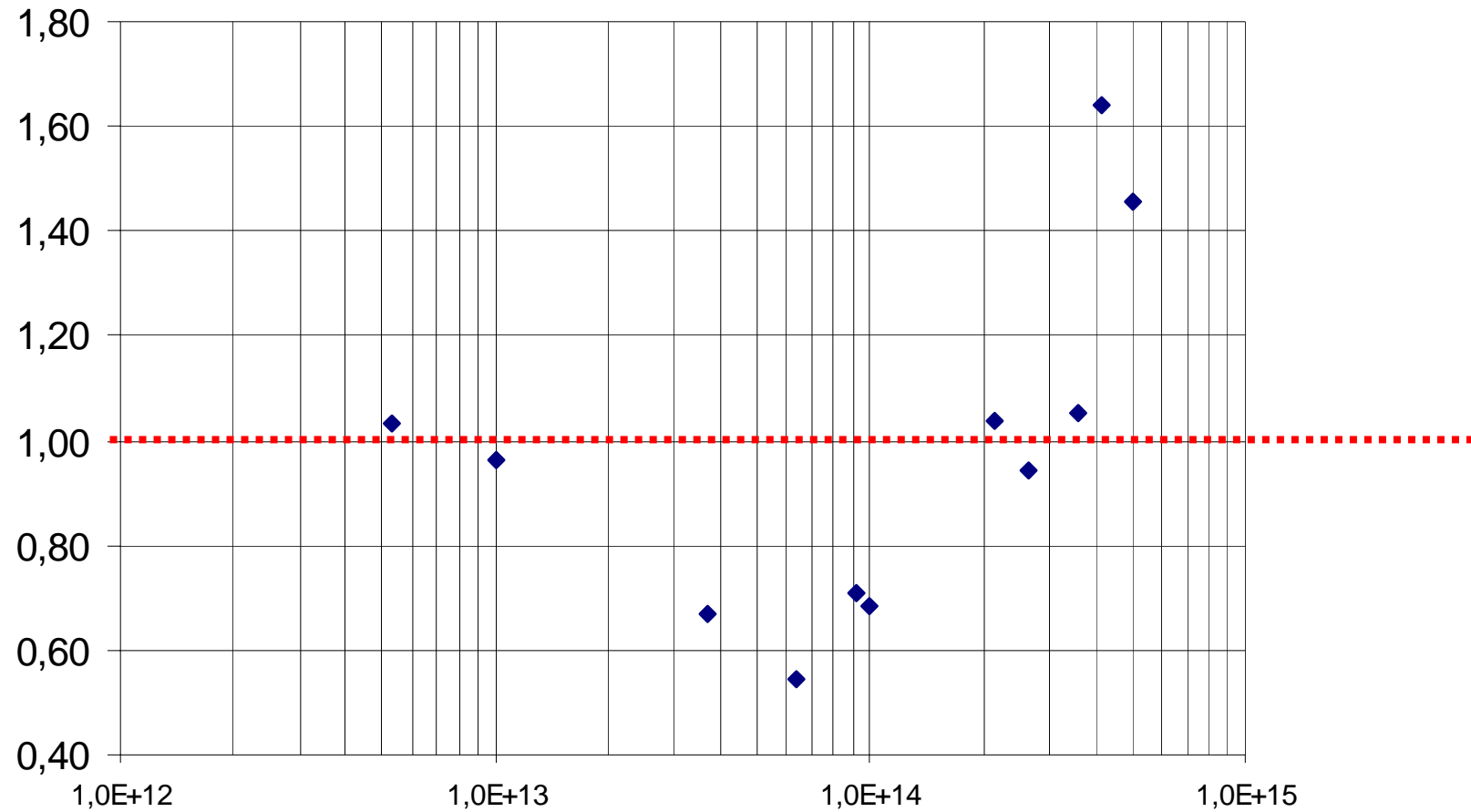
See talk by Esa Tuovinen at 3rd RD50 Workshop
<http://rd50.web.cern.ch/RD50/3rd-workshop/>

TD generation

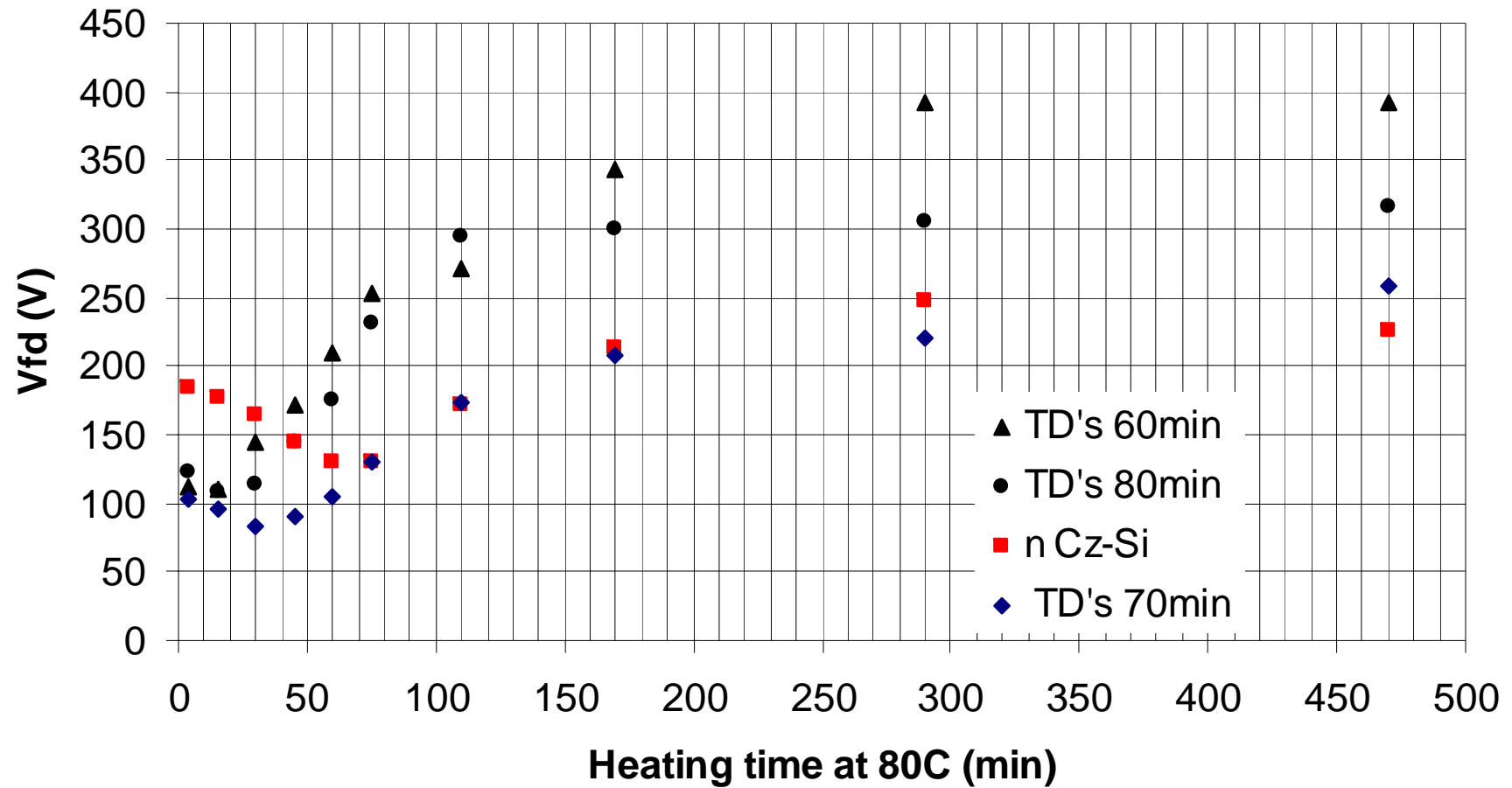


24 GeV/c irradiation

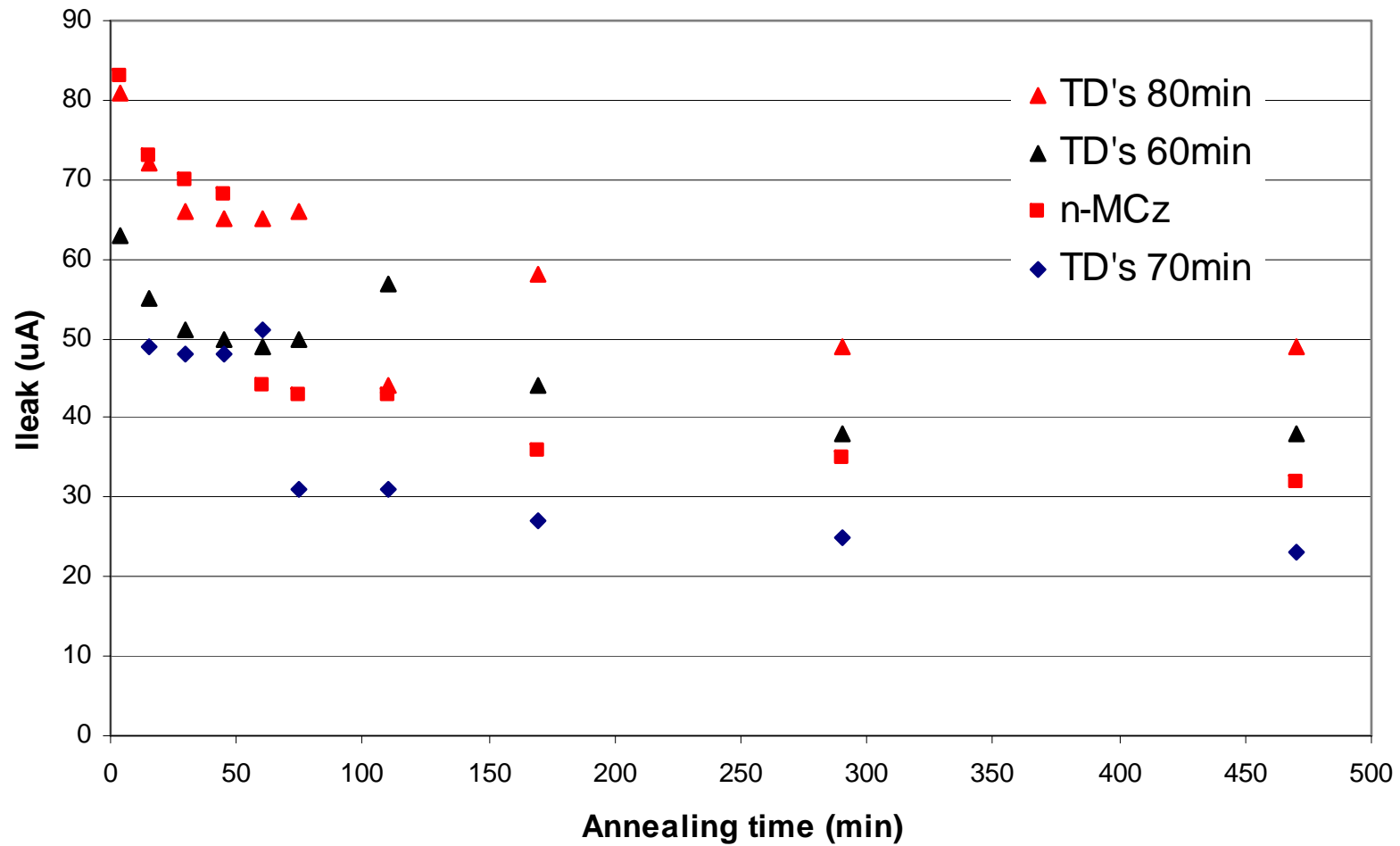
Vfd_irrad/Vfd_preirrad



Annealing



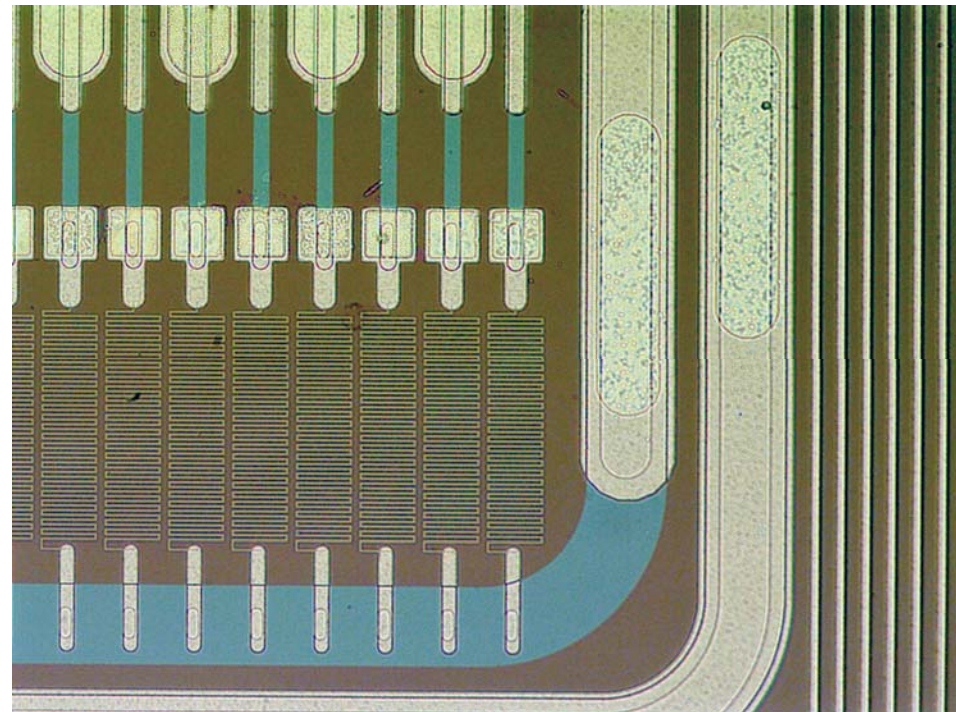
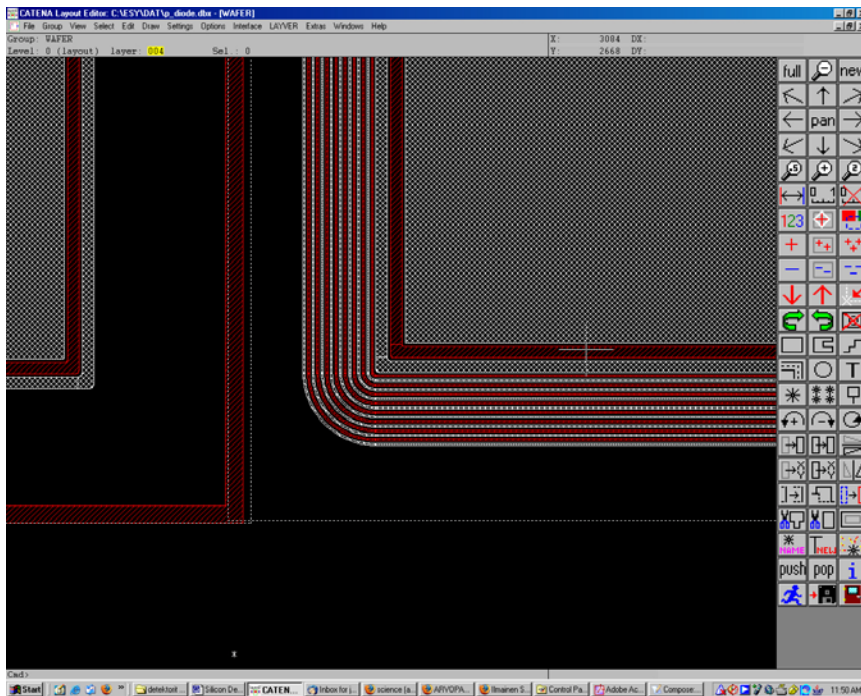
Annealing



Mask sets in Helsinki

N-well pad detector

AC-coupled strip detector
-768 strips & 128 strips minis
-p80 μ m w20 μ m



Higher J_{leak} in strips?

